Part Number Customer					
Category	Parameter		Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm		
	2.0	Primary Flat Orientation	{110}+/-1.0 degree	Wafer Vendor	
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor	
	4.0	Secondary Flat Orientation	none	Wafer Vendor	
	5.0	Overall Thickness	636.00 +/- 2.00 μm	ADE, 100%	
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process	
	7.0	Bow	<80.00µm	ADE to ASTM F534, 100%	
	8.0	Warp	<80.00µm		
	9.0	Edge Chips	0	Bright Light, 100% (note 2)	
	10.0	Edge Exclusion	5mm		
	11.0	Lasermarking	On wafer Backside opposite the flat. Dimensions 14mm x 1.8mm. See attachment		
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor	
	13.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor	
	14.0	Handle Thickness	626.00 +/- 1.50 μm	ADE, 100%	
	15.0	Handle Doping Type	Any	Wafer Vendor	
	16.0	Handle Dopant	Any	Wafer Vendor	
	17.0	Handle Resistivity	0.005 ~ 10 Ohmem	Wafer Vendor	
	18.0	Backside Finish	Polished with lasermark and oxide.	Guaranteed by process	
BuriedOxide	19.0	Oxide Type	Thermal		
	20.0	Oxide Thickness	2,000.00 +/- 100.00 A	Nanospec centre point, 4%	
	21.0	Oxide formed on	Handle and / or device wafer		
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor	
	23.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor	
	24.0	Nominal Thickness	10.00 +/- 0.50 μm	FTIR, 100% 9-Pt (note3)	
	25.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process	
	26.0	Device Doping Type	Any	Wafer Vendor	
	27.0	Device Dopant	Any	Wafer Vendor	
	28.0	Device Resistivity	0.005 ~ 10 Ohmem	Wafer Vendor	
	29.0	Voids	none	Bright Light, 100% (note 2)	
	30.0	Scratches	0	Bright Light, 100% (note 2)	
	31.0	Haze	none	Bright Light, 100% (note 2)	

Icemos Technology Ltd

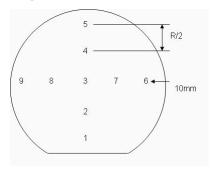
**Product Specification** 

1000.701401

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.			

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information